

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	341	438/305.ccls. and (plural or multiple or third or plurality) near2 (region or area or doping or concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 09:43
L2	4	"5866460".pn. "5739066".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 09:44
L3	13	(US-20020195626-\$ or US-20010018255-\$).did. or (US-5424234-\$ or US-5637514-\$ or US-5739066-\$ or US-5866460-\$ or US-6258680-\$ or US-6274906-\$ or US-6380053-\$ or US-5132757-\$ or US-5183771-\$ or US-6552394-\$ or US-6844252-\$).did.	US-PGPUB; USPAT	OR	ON	2007/05/10 10:10
L5	395	438/163.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 10:10
L6	125	438/174.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 10:49
L7	54	438/185.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 10:49
L8	77	438/194.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 10:56
L9	298	438/230.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 10:56
L11	621	438/231.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 10:56

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L12	419	438/232.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 11:10
L13	663	438/306.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 11:23
L14	341	438/305.ccls. and (plural or multiple or third or plurality) near2 (region or area or doping or concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 12:49
L15	168	438/217.ccls. and (plural or multiple or third or plurality) near2 (region or area or doping or concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 11:43
L16	89	438/217,289,305.ccls. and (source or drain) near10 (plural or plurality or multi or multiple or sequential or several) near5 implant\$5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 12:06
L17	597	438/217,289,305.ccls. and (source or drain) near6 (implant\$4 or diffus\$4) near6 (sidewall or side near wall or spacer or conformal or wall) and (fet or mos or mosfet or nmos or pmos or cmos or transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 12:50
L18	417	438/217,289,305.ccls. and (idd or lightly near doped near drain or drain near extension or source near extension) near10 implant\$5 near10 (sidewall or side near wall or spacer or edge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 12:16
L19	812	438/217,289,305.ccls. and (source or drain or impurity) near6 (implant\$4 or diffus\$4) near6 (sidewall or side near wall or spacer or conformal or wall)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 12:49
L20	1172	257/e29.266.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 12:49
L21	233	257/e29.266.ccls. and (plural or multiple or third or plurality) near2 (region or area or doping or concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 12:50

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L23	304	257/e29.266.ccls. and (source or drain) near6 (implant\$4 or diffus\$4) near6 (sidewall or side near wall or spacer or conformal or wall) and (fet or mos or mosfet or nmos or pmos or cmos or transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 12:51
L24	168	257/E21.409.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 13:17
L25	188	257/E21.435.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 13:17
L26	52	(ldd or lightly near doped near drain or drain near extension or source near extension) near10 (plural or plurality or multi or multiple or sequential or several or three or third) near3 implant\$5 and (conformal or sidewall or spacer or side near wall) near5 (anneal\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 13:18
L27	194	(ldd or lightly near doped near drain or drain near extension or source near extension) near10 (plural or plurality or multi or multiple or sequential or several or three or third) near3 implant\$5 and implant\$5 near8 (sidewall or side near wall or spacer or edge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 13:39
L28	649	gate and source and drain and (source or drain or ldd) near3 (graded or grading or (plural or multiple or plurality or third or three or several) near2 (areas or regions or subregions or portions)) and (sidewall or side adj wall or spacer) near4 (implant or implanting or implanted)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 13:33
L29	68	(ldd or mildd) and (gate or polysilicon) near5 (round or rounded or rounding) near8 (anneal or annealed or annealing or oxidation or oxidizing or oxidate or oxidize or oxidized)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 13:40
L30	37	((multiple near implant\$2) near2 (ldd or lightly near doped near drain) or mildd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 13:54
L32	105	(multiple or plural or several or multi or plurality) near2 (implant\$4 or dopant or doped) near6 ((ldd or lightly near doped near drain) or mildd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 13:56
L33	298	(ldd or lightly near doped near drain) and (implant\$5) near5 (side or wall or sidewall) and (conformal\$3) near6 (oxide or sio or silicon adj dioxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/10 13:57